Low Noise Transistors PNP Silicon

MAXIMUM RATINGS



ON Semiconductor®

Rating	Symbol
Collector - Emitter Voltage	V _{CEO}
Collector - Base Voltage	V _{CBO}
Emitter – Base Voltage	V _{EBO}
Collector Current — Continuous	Ι _C
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	PD
Operating and Storage Junction Temperature Range	T _J , T _{stg}
THERMAL CHARACTERISTIC	s
Characteristic	Symbol
Thermal Resistance, Junction to Ambient	R _{0JA}
Thermal Resistance, Junction to Case	R _{θJC}
	2

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = –10 mAdc, I _B = 0) BC559 BC560	V _{(BR)CEO}	-30 -45			Vdc
Collector – Base Breakdown Voltage $(I_C = -10 \ \mu Adc, I_E = 0)$ BC559 BC560	V _{(BR)CBO}	-30 -50	_		Vdc
Emitter – Base Breakdown Voltage $(I_E = -10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	-5.0		_	Vdc
Collector Cutoff Current ($V_{CB} = -30$ Vdc, $I_E = 0$) ($V_{CB} = -30$ Vdc, $I_E = 0$, $T_A = +125^{\circ}C$)	I _{CBO}			-15 -5.0	nAdc µAdc
Emitter Cutoff Current ($V_{EB} = -4.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	—	_	-15	nAdc

BC559

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS				1		
DC Current Gain		h _{FE}				
(I _C = $-10 \ \mu Adc$, V _{CE} = $-5.0 \ Vdc$)	BC559B BC559C/560C		100 100	150 270	—	
(I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc)	BC559B		180	290	460	
	BC559C/560C BC559		380 120	500 —	800 800	
Collector – Emitter Saturation Voltage		V _{CE(sat)}				Vdc
$(I_{\rm C} = -10 \text{ mAdc}, I_{\rm B} = -0.5 \text{ mAdc})$			-	-0.075	-0.25	
$(I_{C} = -10 \text{ mAdc}, I_{B} = \text{see note 1})$ $(I_{C} = -100 \text{ mAdc}, I_{B} = -5.0 \text{ mAdc}, \text{see not})$	e 2)		_	-0.3 -0.25	-0.6 —	
Base-Emitter Saturation Voltage (I _C = -100 mAdc, I _B = -5.0 mAdc)		V _{BE(sat)}	-	-1.1	_	Vdc
Base-Emitter On Voltage		V _{BE(on)}				Vdc
$(I_{C} = -10 \ \mu Adc, V_{CE} = -5.0 \ Vdc)$			—	-0.52	A	
(I _C = −100 μAdc, V _{CE} = −5.0 Vdc) (I _C = −2.0 mAdc, V _{CE} = −5.0 Vdc)			-0.55	-0.55 -0.62	-0.7	
SMALL-SIGNAL CHARACTERISTICS			•	, C		•
Current Coin Pondwidth Broduct				050		MLI-

$\label{eq:current-Gain} \begin{array}{c} Current-Gain - Bandwidth \mbox{ Product} \\ (I_C = -10 \mbox{ mAdc}, \mbox{ V}_{CE} = -5.0 \mbox{ Vdc}, \mbox{ f} = 100 \mbox{ MHz}) \end{array}$	fT		250	7-	MHz
Collector-Base Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{cbo}		2.5	_	pF
$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	h _{fe}	240 450	330 600	500 900	_
	NF ₁ NF ₂		0.5	2.0 10	dB
NOTES: 1. I _B is value for which I _C = -11 mA at V _{CE} = -1.0 V. 2. Pulse test = 300 μs - Duty cycle = 2%.					

BC559

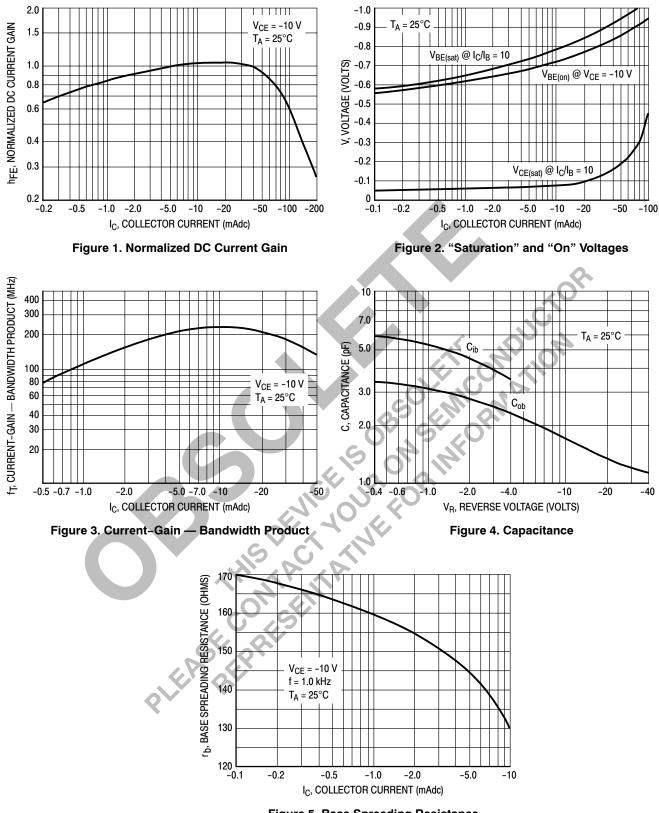
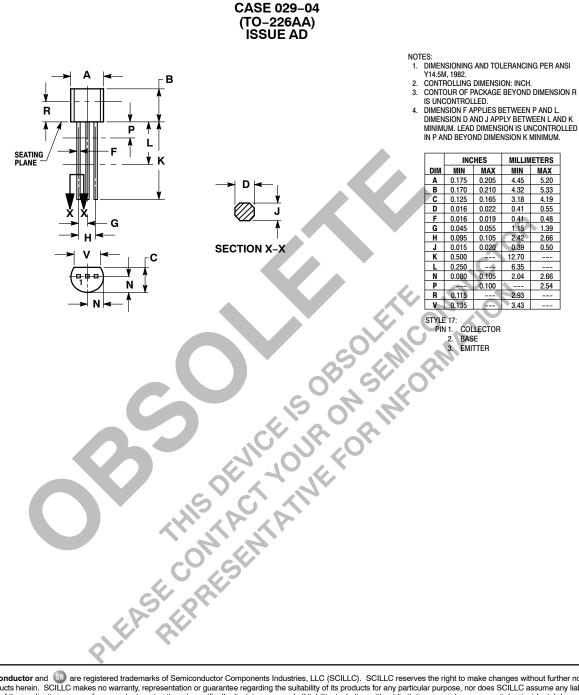


Figure 5. Base Spreading Resistance

BC559

PACKAGE DIMENSIONS



ON Semiconductor and IIII are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typical" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunit//Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Europe, Middle East and Africa Techr Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5773–3850 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative